

SMB Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMB(DO-214AA)

HF RoHS



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS1045B -6AF	SS1060B -6AF	SS10100B -6AF	SS10150B -6AF	SS10200B -6AF	Unit 单位
Marking 印字		SS1045	SS1060	SS10100	SS10150	SS10200	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	45	60	100	150	200	V
DC Reverse Voltage 直流反向电压	V_R	45	60	100	150	200	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	32	42	70	105	140	V
Forward Rectified Current 正向整流电流	I_F	10					A
Peak Surge Current 峰值浪涌电流	I_{FSM}	175					A
Thermal Resistance J-L 结到管脚热阻	$R_{\theta JL}$	16					$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150					$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	$-55\text{to}+150^{\circ}\text{C}$					$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS1045B -6AF	SS1060B -6AF	SS10100B -6AF	SS10150B-6AF SS10200B-6AF	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.55	0.70	0.85	0.92	V	I _F =10A
Reverse Current 反向电流	I _R (25℃) (125℃)	0.1 5		0.02 2		mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	440				pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

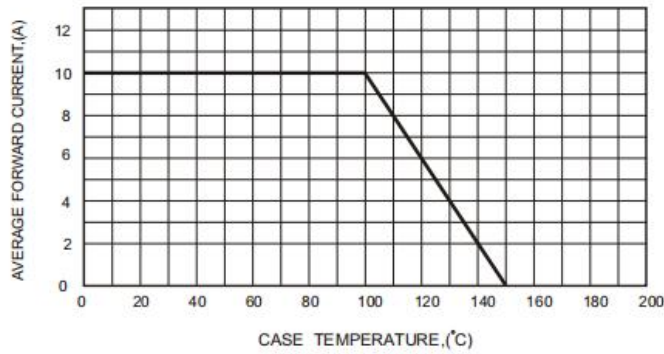


FIG.2-TYPICAL FORWARD CHARACTERISTICS

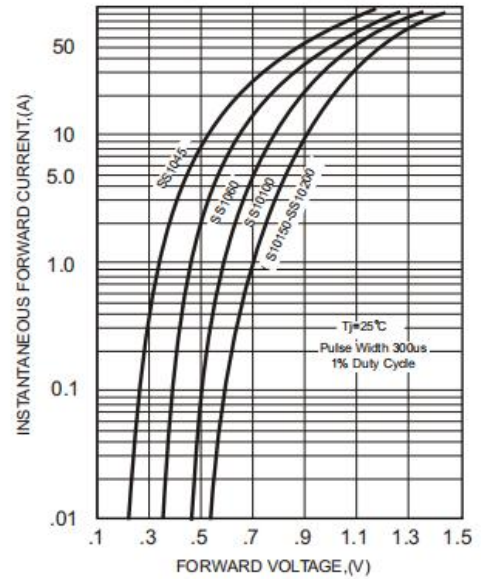


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

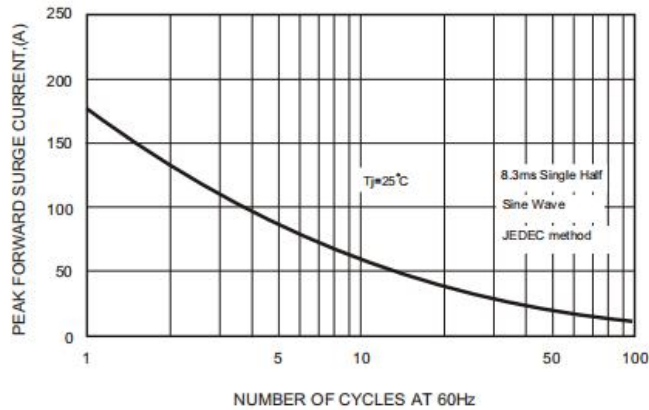


FIG.4-TYPICAL JUNCTION CAPACITANCE

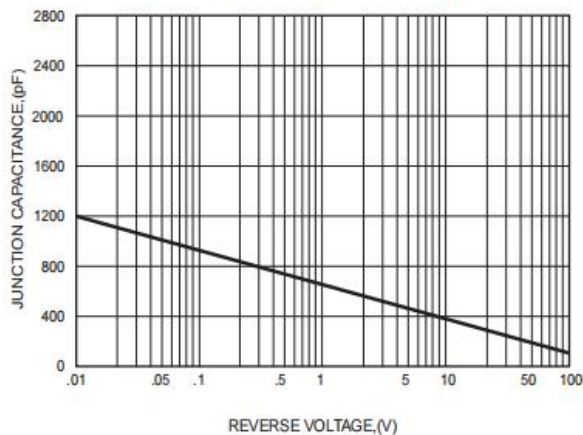
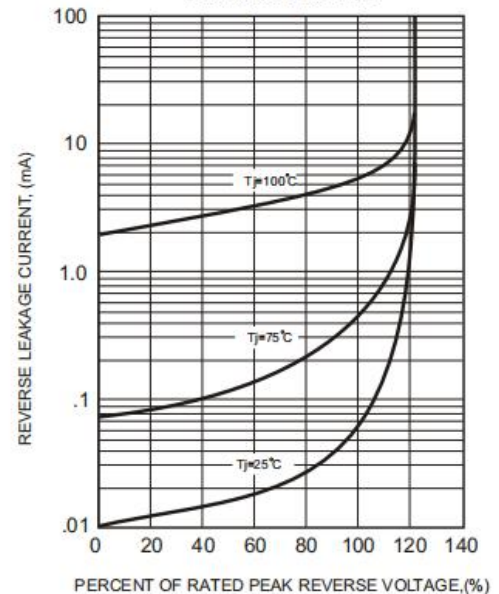
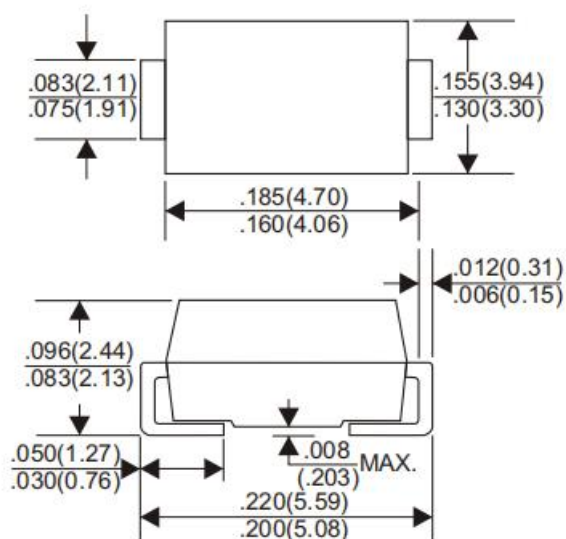


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in inches and (millimeters)